

Features

- SOT-23 Package For surface mount application
- Protects from line to V_{CC} and line to ground
- Low forward voltage and reverse recovery characteristics
- Bidirectional-low-forward available with "-04" suffix (Figure 2)
- Tape & Reel EIA Standard 481.

Mechanical Data

- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0 and MSL Rating 1
- Mounting Position: Any
- Weight: .008 grams (approx.)

MAXIMUM RATINGS

- Operating Temperature: -55°C to +125°C
- Storage Temperature: -55°C to +150°C
- Power Dissipation: 200 mWatts @ T_{amb}=25°C
- Forward Continuous Current: $BAS40 I_{FM} = 200 \text{mA} @ T_a = 25^{\circ}\text{C}$ BAS70 $I_{FM} = 70 \text{mA} @ T_a = 25^{\circ}\text{C}$
- Surge Forward Current: 600mA @ t_p<1s, T_{amb}=25^oC

DESCRIPTION

Various configurations of Schottky barrier's diodes in SOT-23 package are provided for general-purpose use in high-speed switching ,mixers and detector applications. They may also be used for signal integrity and counteract the transmission-line effects with (PC) board trances by clamping over/and undershoot from signal reflections with the schottky-low-threshold voltages.

This type of termination also does not depend on matching the transmission line characteristic impedance, making it particularly useful where line impendance is unknown or a variable. This methode of termination can control distortions of clock, data, address, and control lines as well as provides a stabilizing effect on signal jitter. It can also significantly reduce power consumption compared to standard resistor-based termination methods.

BAS40 THRU BAS70

Surface Mount

Schottky Barrier Diode

200 mWatt



BAS40 and BAS70

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DEVICE TYPE	FIGURE	Repetitive Peak Reverse Voltage	Reverse Breakdown Voltage Tested with 10µA Pulse	Leakage Current Pulse test tp < 300 μ s @ For BAS40 V _R = 30 V For BAS70 V _R = 50 V I _R (nA)		Forward Voltage Pulse Test tp < 300µs at I _F = 1 mA at I _F = 40 mA V_F (mV)			Reverse Recovery Time from $I_F = 10 \text{ mA}$ through $I_R=10\text{mA}$ to $I_R=1\text{mA}$	Thermal Resistance Junction to Ambient Air	Capacitance At $V_R = 0V$ F = 1 MHz C _{tot}
		V _{RRM} (VOLTS)	V _{(BR)R} (VOLTS)						t _{rr} (ns)	R _{thJA} (K/W)	pF
		TYP	MIN	TYP	MAX	I _F =1mA	I _F =15mA	I _F =40mA	MAX	MAX	MAX
BAS40	1	40	40	20	200	380		1000	5	430	5
BAS40-04	2	40	40	20	200	380		1000	5	430	5
BAS40-05	3	40	40	20	200	380		1000	5	430	5
BAS40-06	4	40	40	20	200	380		1000	5	430	5
BAS70	1	70	70	20	200	410	1000		5	430	2
BAS70-04	2	70	70	20	200	410	1000		5	430	2
BAS70-05	3	70	70	20	200	410	1000		5	430	2
BAS70-06	4	70	70	20	200	410	1000		5	430	2

ELECTRICAL CHARACTERISTICS PER DIODE @ 25⁰C Unless otherwise specified



Ordering Information

Device	Packing
(Part Number)-TP	Tape&Reel3Kpcs/Reel

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